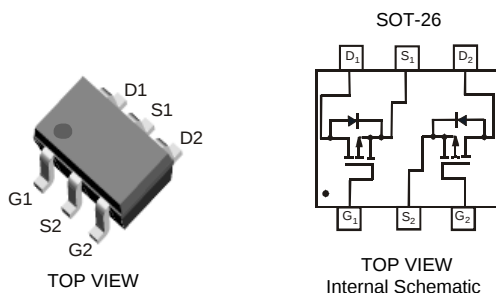


Features

- Dual P-Channel MOSFET
- Low On-Resistance
 - 150 mΩ @ $V_{GS} = -4.5V$
 - 200 mΩ @ $V_{GS} = -2.5V$
 - 240 mΩ @ $V_{GS} = -1.8V$
- Very Low Gate Threshold Voltage $V_{GS(th)} \leq 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe.
Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.015 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	± 12	V
Drain Current (Note 1)	$T_A = 25^\circ C$	I_D	-2.0	A
	$T_A = 70^\circ C$		-1.5	
Pulsed Drain Current		I_{DM}	-7	A

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_D	600	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	208	$^\circ C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	$^\circ C$

Notes:

1. Device mounted on FR-4 PCB.
2. No purposefully added lead.
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0 -5.0	μA	T _J = 25°C T _J = 125°C V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	-0.45	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	92	150	mΩ	V _{GS} = -4.5V, I _D = -2.0A
			134	200		V _{GS} = -2.5V, I _D = -1.5A
			180	240		V _{GS} = -1.8V, I _D = -0.5A
			—	—		V _{DS} = -10V, V _{GS} = -810mA
Forward Transconductance	g _{FS}	—	3.1	—	S	V _{DS} = -10V, V _{GS} = -810mA
Diode Forward Voltage (Note 4)	V _{SD}	—	—	-0.9	V	V _{GS} = 0V, I _S = -0.5A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	320	—	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	80	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	60	—	pF	
Turn-On Delay Time	t _{D(on)}	—	11.51	—	ns	V _{DS} = -10V, V _{GS} = -4.5V R _G = 6Ω, R _L = 10Ω
Turn-On Rise Time	t _r	—	12.09	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	55.34	—	ns	
Turn-Off Fall Time	t _f	—	27.54	—	ns	

Notes: 4. Short duration pulse test used to minimize self-heating effect.

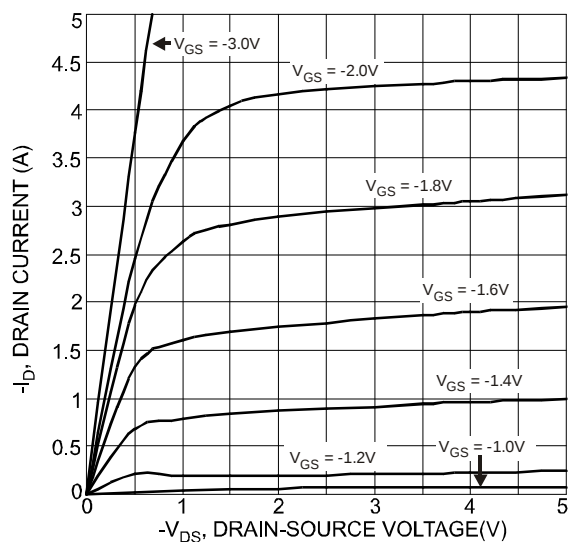


Fig. 1 Typical Output Characteristics

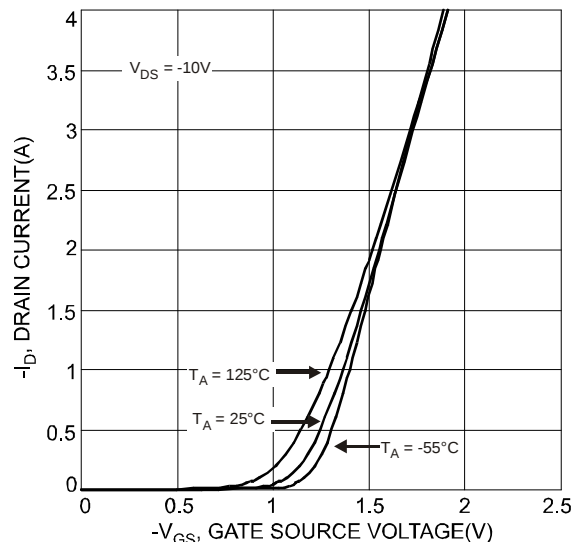


Fig. 2 Typical Transfer Characteristics

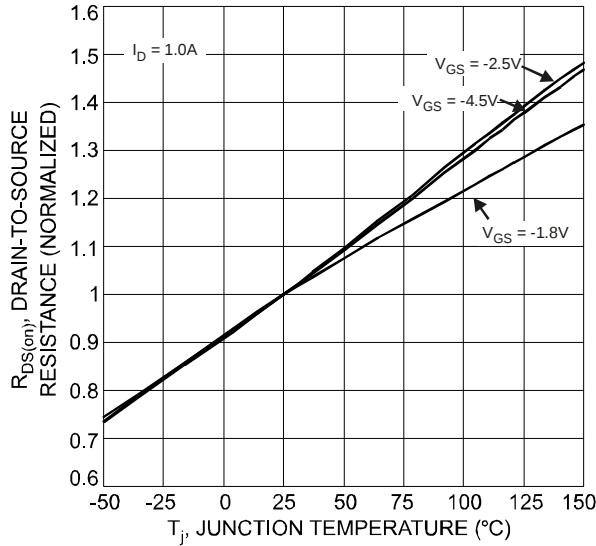


Fig. 3 On-Resistance Variation with Temperature

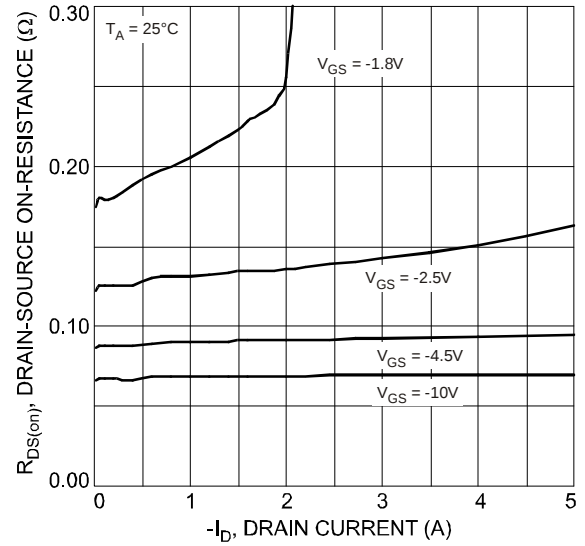


Fig. 4 On-Resistance vs Drain Current and Gate Voltage

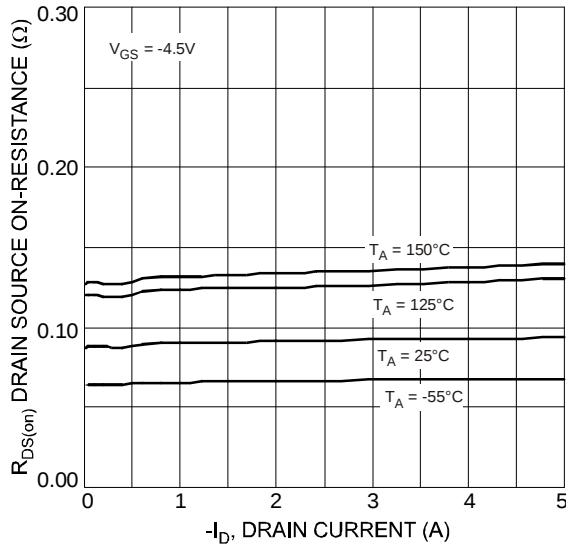


Fig. 5 Drain-Source On-Resistance Vs. Drain Current and Temperature

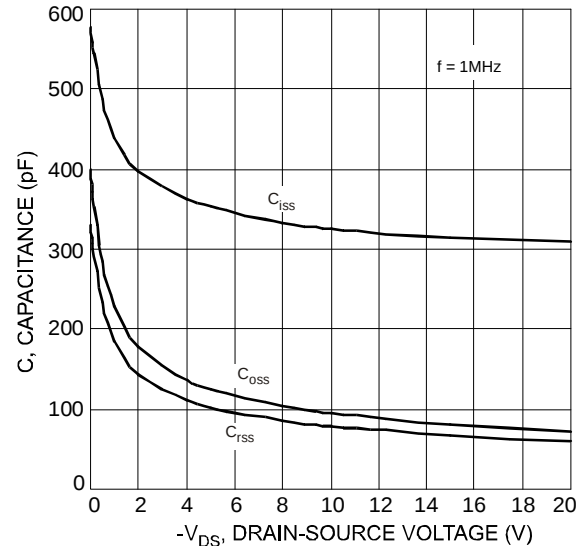


Fig. 6: Typical Capacitance

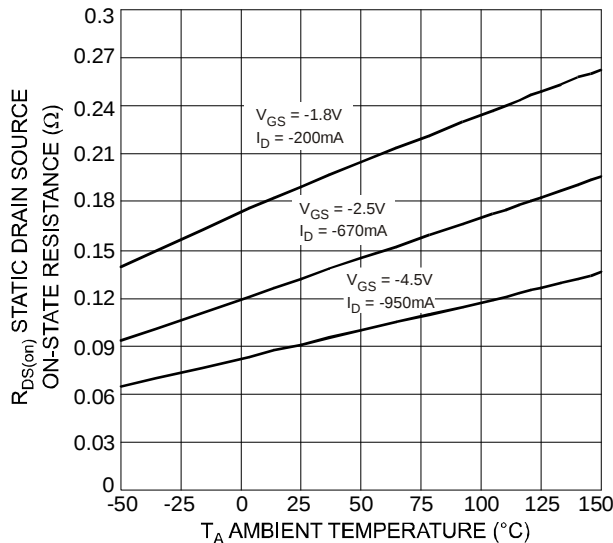


Fig. 7 Static Drain-Source On-State Resistance vs Ambient Temperature

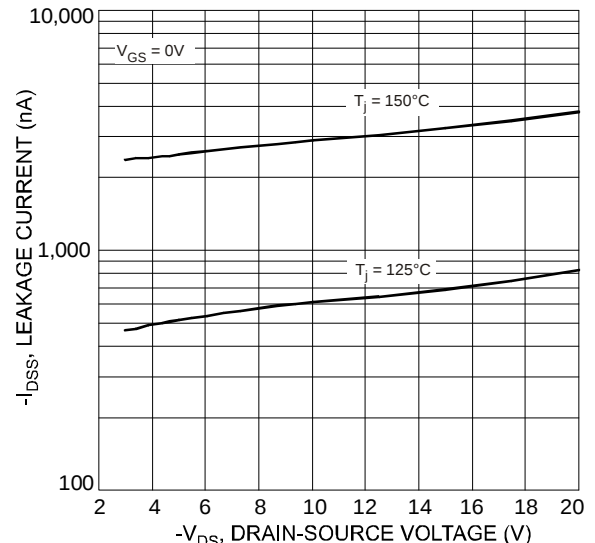


Fig. 8 Drain-Source Leakage Current vs Voltage

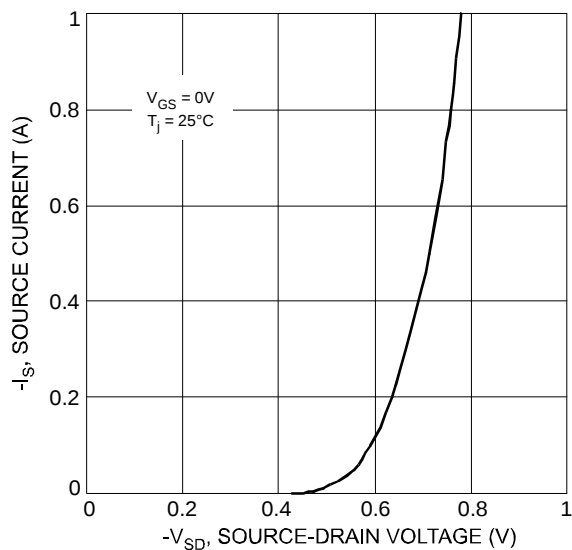


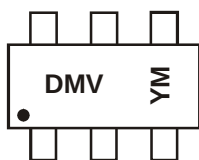
Fig. 9 Diode Forward Voltage vs. Current

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2240UDM-7	SOT-26	3000/Tape & Reel

 Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



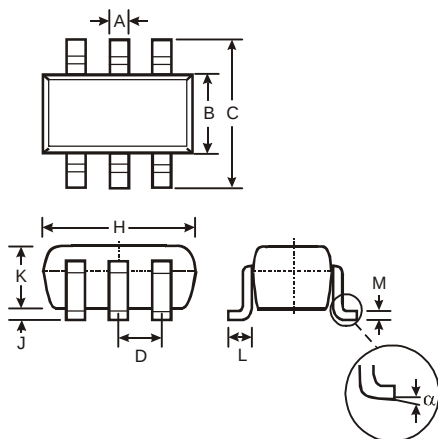
DMV = Marking Code
 YM = Date Code Marking
 Y = Year (ex: U = 2007)
 M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012
Code	U	V	W	X	Y	Z

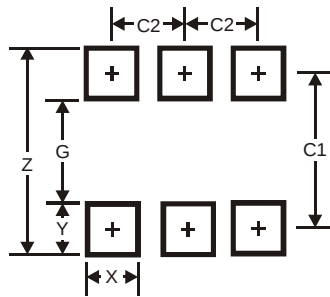
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95

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